L Number	Hits	Search Text	DB	Time stamp
1	273	(gate with germanium) same $4silicon same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
2	87	((gate with germanium) same $4silicon same nitride) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
3	3	((polysilicon with over with germanium with gate) same nitride) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:41
4	2	((polysilicon with top with germanium with gate) same nitride) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:41
5	76	(((gate with germanium) same $4silicon same nitride) and (@ad<19990623 or @rlad<19990623)) and dop$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
6	99	(gate with germanium) same $4silicon same nitride same dop$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
7	32	((gate with germanium) same $4silicon same nitride same dop$3) and (@ad<19990623 or @rlad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
–	212	(gate adj1 electrode) with germanium	USPAT; EPO; JPO; DERWENT	2004/03/03 16:16
–	2	((gate adj1 electrode) with germanium) same (conduct$3 adj1 film)	USPAT; EPO; JPO; DERWENT	2002/01/23 10:26
–	13	((gate adj1 electrode) with germanium) and (conduct$3 adj1 film)	USPAT; EPO; JPO; DERWENT	2002/01/23 10:26
–	9	((gate adj1 electrode) with germanium) same (p-type near3 dop$3)	USPAT; EPO; JPO; DERWENT	2002/01/23 16:26
–	2	((gate adj1 electrode) with germanium) same (silicon adj1 substrate) same MOSFET	USPAT; EPO; JPO; DERWENT	2002/01/24 08:55
–	31	((gate adj1 electrode) with germanium) and (silicon adj1 substrate) and MOSFET	USPAT; EPO; JPO; DERWENT	2002/01/24 10:23
–	11	"5216271"	USPAT; EPO; JPO; DERWENT	2002/01/31 13:12
–	8	"5101247"	USPAT; EPO; JPO; DERWENT	2002/01/31 13:49
–	2511	conduct$3 with (transition near3 metal)	USPAT; JPO; DERWENT	2002/01/31 15:42
–	0	(conduct$3 with (transition near3 metal)) and (gate near4 germanium)	USPAT; JPO; DERWENT	2002/01/31 15:38
–	9	(conduct$3 with (transition near3 metal)) and gate and germanium	USPAT; JPO; DERWENT	2002/01/31 15:24
–	0	(conduct$3 with (transition near3 metal)) same (gate and germanium)	USPAT; JPO; DERWENT	2002/01/31 15:40
–	104	(conduct$3 with (transition near3 metal)) and (metal near2 silicide)	USPAT; JPO; DERWENT	2002/01/31 15:40
–	407	(conduct$3 near3 (film or layer)) with (transition near3 metal)	USPAT; JPO; DERWENT	2002/01/31 15:59

–	931	(germanium near2 (film or layer)) and (conduct$3 near2 (film or layer))	USPAT; JPO; DERWENT	2002/02/01 10:33
–	35609	(polysilicon near2 (layer or film))	USPAT; JPO; DERWENT	2002/02/01 10:27
–	150	((polysilicon near2 (layer or film))) and ((germanium near2 (film or layer)) and (conduct$3 near2 (film or layer)))	USPAT; JPO; DERWENT	2002/02/01 10:31
–	0	"polysilicon layer between a germanium layer and a conducitive layer"	USPAT; JPO; DERWENT	2002/02/01 10:33
–	158	(germanium near2 (film or layer)) with (conduct$3 near2 (film or layer))	USPAT; JPO; DERWENT	2002/02/01 11:18
–	11	((germanium near2 (film or layer)) with (conduct$3 near2 (film or layer))) with (polysilicon near2 (layer or film))	USPAT; JPO; DERWENT	2002/02/01 10:36
–	6	((germanium near2 (film or layer)) with (conduct$3 near2 (film or layer))) with silicide	USPAT; JPO; DERWENT	2002/02/01 11:00
–	1676	(germanium near2 (film or layer)) with ($4silicon near2 (film or layer))	USPAT; JPO; DERWENT	2002/02/01 11:23
–	35	((germanium near2 (film or layer)) with ($4silicon near2 (film or layer))) with silicide	USPAT; JPO; DERWENT	2002/02/01 11:23
–	12	"5608249"	USPAT; JPO; DERWENT	2002/02/01 14:09
–	83	(gate adj (dielectric or insulator)) with (germanium or ge)	USPAT; EPO; JPO; DERWENT	2002/09/15 19:03
–	67	((gate adj (dielectric or insulator)) with (germanium or ge)) and @ad<19992306	USPAT; EPO; JPO; DERWENT	2002/09/15 19:05
–	58	((gate adj (dielectric or insulator)) with (germanium or ge)) and @ad<19990623	USPAT; EPO; JPO; DERWENT	2002/09/22 09:08
–	18	((germanium or ge) adj (film or layer)) with (gate adj insulat$3)	USPAT; EPO; JPO; DERWENT	2002/09/19 15:59
–	16	(((germanium or ge) adj (film or layer)) with (gate adj insulat$3)) and @ad<19990623	USPAT; EPO; JPO; DERWENT	2002/09/19 16:00
–	19	(((gate adj electrode) with (germanium or ge)) and @ad<19990623) and ((gate adj (insulator or dielectric)) with (germanium or ge))	USPAT; EPO; JPO; DERWENT	2002/09/22 09:11
–	382	((gate adj electrode) with (germanium or ge)) and @ad<19990623	USPAT; EPO; JPO; DERWENT	2002/09/22 09:27
–	157	((gate adj1 electrode) with (germanium or ge)) same (gate adj (dielectric or insulat$3 or $2oxide)) and (dop$3 same ("p-type" or boron or b or al or aluminum or ga or in))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 14:01
–	44	(((gate adj1 electrode) with (germanium or ge)) same (gate adj (dielectric or insulat$3 or $2oxide)) and (dop$3 same ("p-type" or boron or b or al or aluminum or ga or in))) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:30
–	0	(germanium near3 gate) same "1.times.10.sup.$2"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:21
–	3	(germanium near3 gate) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; DERWENT	2003/04/11 15:25

—	3	(germanium with gate with electrode) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:00
—	20	(germanium with film) same "p-type" same impurities same dop$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 15:29
—	15	((germanium with film) same "p-type" same impurities same dop$3) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:00
—	44	(germanium with film) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:13
—	19	((germanium with film) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:12
—	701	(ge or germanium) with "above" with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:12
—	519	((ge or germanium) with "above" with oxide) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:00
—	7	(((ge or germanium) with "above" with oxide) and @ad<19990623) and ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:08
—	13	(((ge or germanium) with "above" with oxide) and @ad<19990623) and (gate adj (dielectric or oxide or insulat$3)) and (gate adj electrode) and "p-type"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 16:58
—	0	(germanium adj gate adj electrode) with "on" with (insulat$3 or oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:00
—	27	germanium adj gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:00
—	3	(germanium adj gate adj electrode) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:17
—	45	((ge or germanium) with electrode) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; .DERWENT	2003/04/11 17:18
—	33	(((ge or germanium) with electrode) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:40
—	3	((ge or germanium) with electrode with gate) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:31

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-	5	((ge or germanium) with gate) same ("p-type" or boron) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:34
-	2	(germanium same (metal adj silicide) same polysilicon same (gate adj electrode)) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 17:42
-	36	(germanium same (metal adj silicide) same polysilicon) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 18:03
-	50	(germanium with (work adj function)) same (silicon with (work adj function))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 18:13
-	17	germanium with (work adj function) with "ev"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/04/11 18:14
-	283	((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or aluminum or indium or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:49
-	41	(((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or aluminum or indium or gallium)) and ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:50
-	20	((((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or aluminum or indium or gallium)) and ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:21
-	814	(gate adj1 electrode) with (germanium or ge)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:49
-	8	((gate adj1 electrode) with (germanium or ge)) same ("1.times.10.sup.17" or "1.times.10.sup.18" or "1.times.10.sup.19" or "1.times.10.sup.20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 17:55
-	2	("5952701" | "6262456" | "2002/0113294").PN.	USPAT	2003/08/13 17:52
-	2	(work adj function) same (germanium or ge) same (mid with gap with energy with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:19
-	0	1111686.URPN.	USPAT	2003/08/13 18:05
-	5	("4984043" | "4990974" | "5194923" | "5250818" | "5619057").PN.	USPAT	2003/08/13 18:05
-	39	(boron or b) with implant$5 with (germanium or ge) with "kev"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:20
-	20	((boron or b) with implant$5 with (germanium or ge) with "kev") and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:21
-	31	(dop$3 or implant$5) with (germanium or ge) with (gate adj electrode) with (boron or b)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:46

-	13	((dop$3 or implant$5) with (germanium or ge) with (gate adj electrode) with (boron or b)) and @ad<19990623	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/13 18:46
-	0	jp-27854-$.did	USPAT; EPO; JPO; DERWENT	2003/08/22 11:24
-	0	jp-1027854-$.did	USPAT; EPO; JPO; DERWENT	2004/02/19 11:57
-	0	jp-027854-$.did	USPAT; EPO; JPO; DERWENT	2004/02/19 11:57
-	0	jp-027854-$.did.	USPAT; EPO; JPO; DERWENT	2004/02/19 11:58
-	2	jp-10027854-$.did.	USPAT; EPO; JPO; DERWENT	2004/02/19 11:58